# MCR12DG, MCR12MG, MCR12NG

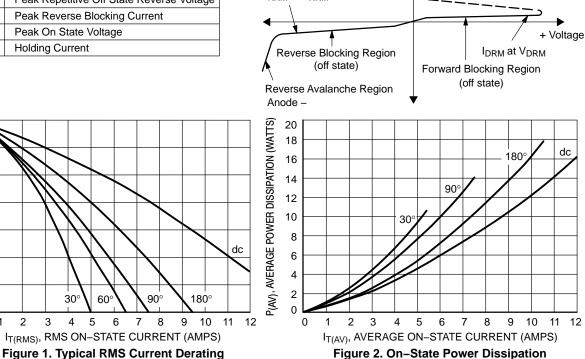
### THERMAL CHARACTERISTICS

Characteristic		Value			Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ extsf{ heta}JC} \ R_{ heta}JA$	2.2 62.5 260		°C/W	
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL			°C	
ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}C$ unless otherwise noted)					
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Peak Repetitive Forward or Reverse Blocking Current $(V_D = Rated V_{DRM} and V_{RRM}; Gate Open)$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$ $T_J = 125^{\circ}C$	I <sub>DRM</sub> , I <sub>RRM</sub>			0.01 2.0	mA
ON CHARACTERISTICS					
Peak Forward On–State Voltage (Note 2) (I <sub>TM</sub> = 24 A)	V <sub>TM</sub>	-	-	2.2	V
Gate Trigger Current (Continuous dc) (V <sub>D</sub> = 12 V; $R_L$ = 100 $\Omega$ )		2.0	8.0	20	mA
Holding Current ( $V_D$ = 12 V, Gate Open, Initiating Current = 200 mA)		4.0	20	40	mA
Latch Current ( $V_D$ = 12 V, $I_G$ = 20 mA)		6.0	25	60	mA
Gate Trigger Voltage (Continuous dc) (V <sub>D</sub> = 12 V; R <sub>L</sub> =100 $\Omega$ )		0.5	0.65	1.0	V
DYNAMIC CHARACTERISTICS					
Critical Rate of Rise of Off–State Voltage $(V_D = Rated V_{DRM}, Exponential Waveform, Gate Open, T_J = 125°C)$		100	250	-	V/μs
Repetitive Critical Rate of Rise of On-State Current	di/dt	-	-	50	A/μs

IPK = 50 A, Pw = 40 µsec, diG/dt = 1 A/µsec, Igt = 50 mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Indicates Pulse Test: Pulse Width  $\leq$  2.0 ms, Duty Cycle  $\leq$  2%.

+ Current **Voltage Current Characteristic of SCR** Symbol Parameter тм Peak Repetitive Off State Forward Voltage VDRM on state Peak Forward Blocking Current IDRM Ι<sub>Η</sub> I<sub>RRM</sub> at V<sub>RRM</sub> V<sub>RRM</sub> Peak Repetitive Off State Reverse Voltage Peak Reverse Blocking Current I<sub>RRM</sub> Peak On State Voltage VTM Holding Current  $I_{\rm H}$ **Reverse Blocking Region** (off state) Reverse Avalanche Region Anode -125 20 18 120 T<sub>C</sub>, CASE TEMPERATURE (°C) 16 115 14 90 12 110 10 30 105



Anode +

100

95

90

0 1 30

2

3 4 60°

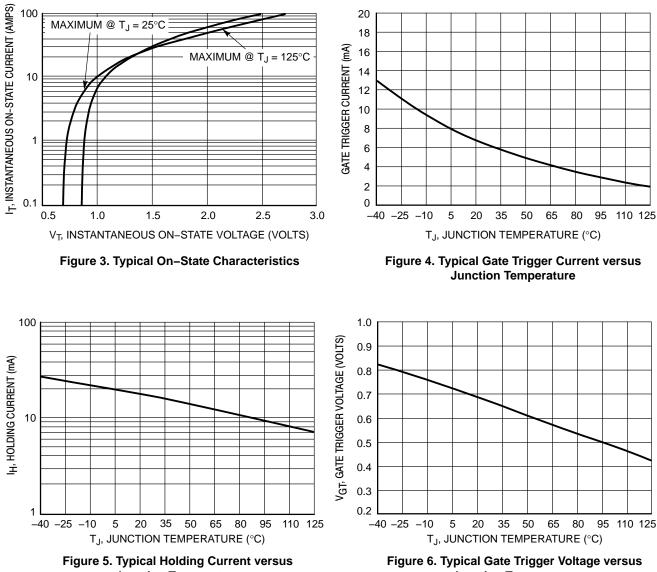
6 7

5

90°

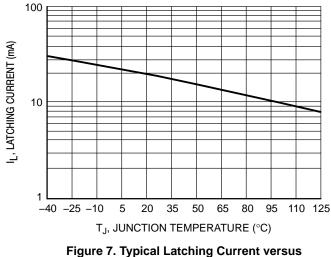
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**Junction Temperature** 

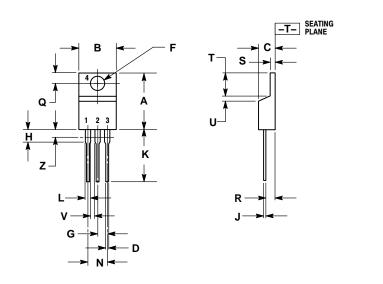
**Junction Temperature** 





#### PACKAGE DIMENSIONS

**TO-220** CASE 221A-09 ISSUE AH



	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MIN MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.61	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
ſ	0.014	0.024	0.36	0.61	
Κ	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
s	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Ζ		0.080		2.04	

DIMENSIONING AND TOLERANCING PER ANSI

Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

> STYLE 3: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE

NOTES

1.

3.

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